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(71) Applicant: SPINNAKER SEMICONDUCTOR, INC. [US/US]; 5705 Lois Lane, Edina, MN 55439 (US).

(72) Inventor: SNYDER, John, P.; 5705 Lois Lane, Edina, MN 55439 (US).

(74) Agents: KRAUS, Jason, R. et al.; Dorsey & Whitney Llp, Pillsbury Center South, 220 South Sixth Street, Minneapolis, MN 55402-1498 (US).

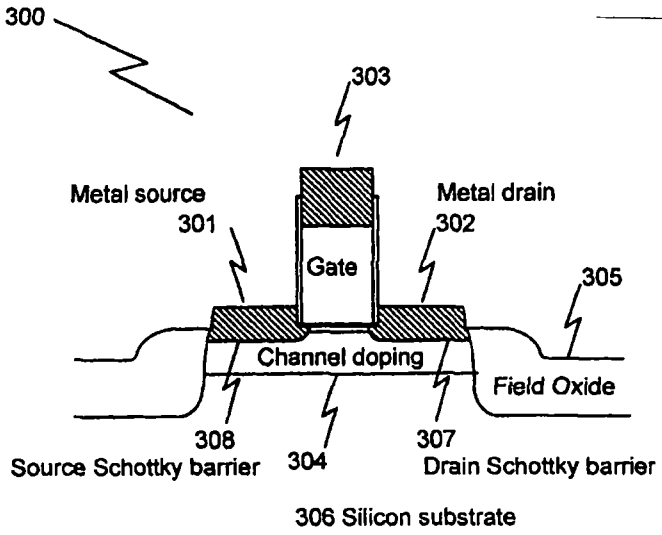
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(54) Title: MOSFET DEVICE SYSTEM AND METHOD



ACTION

(57) Abstract: A MISFEED device system and method of fabricating same are disclosed. The present invention utilizes Shotky barrier contacts (301, 302) for source and/or drain contact fabrication within the context of a MISFEED device structure to eliminate the requirement for halo/pocket implants and shallow source/drain extensions to control short channel effects. Additionally, the present invention unconditionally eliminates the parasitic bipolar gin associated with MISFEED fabrication, reduces manufacturing costs, tightens control of device performance parameters, and provides for superior device characteristics as compared to the prior art.

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